# Enesas Electronics America Inc - R7FS124762A01CLM#AC1 Datasheet



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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	CANbus, I <sup>2</sup> C, SCI, SPI, UART/USART, USB
Peripherals	LVD, POR, PWM, WDT
Number of I/O	25
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 11x14b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	36-WFLGA
Supplier Device Package	36-WFLGA (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r7fs124762a01clm-ac1

S124 Datasheet 1. Overview

# 1.7 Pin Lists

	НМІ	logs	Ana	ces	ion Interfac	ommunicati	Co		ners	Tin					r	Pin numbe		
1		DAC12, ACMPLP		SPI		SCI	USBFS, CAN	RTC		GPT_OPS, POEG			Power, System, Clock, Debug, CAC	LGA36	QFN40	QFN48		LQFP64, QFN64
A,B	TS20 IRQ0				SCL0_A	SCK0_B/ SCK1_B						P400	CACREF_	C2		1	1	1
Second   S	TS19 IRQ5				SDA0_A	S0_B/ SS0_B/ TXD1_B/ MOSI1_B/	CTX0_B					P401		-	-	2	2	2
Section   Sect	TS18 IRQ4					RXD1_B/ MISO1_B/	CRX0_B					P402		-	-	-	-	3
S	TS17					CTS1_RT S1_B/						P403		-	-	-	-	4
Total						221_B							VCL	A1	2	3	3	5
8												P215	XCIN	B1	3	4	4	- 6
9 7 7 6 D3 XTAL P213												P214	XCOUT	C1	4	5	5	7
9 7 7 6 D3 XTAL P213													VSS	D1	5	6	6	8
A_D	IRQ2					TXD1 A/				GTETRG		P213						
B_D   MISO1_M   SCL1_A	IRQ3					MOSI1_A/ SDA1_A				A_D	AGTEE1							
12	11/05					MISO1_A/					AGILLI	1212						
B													VCC					
B	TS07 IRQ4			MOSIA_B		MOSI0_B/ SDA0_B					AGTOA1	P411		-	-	-	-	12
14	TS06 IRQ5			MISOA_B		MISO0_B/					AGTOB1	P410		-	-	-	-	13
15	TS05 IRQ6					TXD9_A/ MOSI9_A/						P409		-	-	10	10	14
16	TS04 IRQ7					RXD9_A/ MISO9_A/						P408		-	9	11	11	15
17	TS03			SSLB3_A	SDA0_B	CTS0_RT S0_D/	USB_VBU S	RTCOUT				P407		E2	10	12	12	16
19						SS0_D							VSS_USB	F1	11	13	13	17
20   16   16   14   F4   VCC_US   B							USB_DM							F2	12	14	14	18
21   17   15   F5   VCC_US   B_LDO							USB_DP							F3	13	15	15	19
21													VCC_US B	F4	14	16	16	20
22													VCC_US	F5	15	17	17	21
23 CLKOUT A P205 AGTO1 GTIV_A GTIOC4A B TXD0_D/ SCL1_A SSLB0_A MOSI0_D/ CTS9_RT S9_A/ SS9_A  24 CACREF_ P204 AGTIO1_ GTIW_A GTIOC4B B SCK0_D/ SCK0_D/ SCK0_B A	TS01 IRQ0			SSLB1_A	SDA1_A	MISO0_D/				GTIU_A		P206	_	-	-	18	18	22
24 CACREF_ P204 AGTIO1_ GTIW_A GTIOC4B SCK0_D/ SCL0_B RSPCKB_ A	TSCAP_A IRQ1			SSLB0_A	SCL1_A	TXD0_D/ MOSI0_D/ SDA0_D/ CTS9_RT S9_A/				GTIV_A	AGTO1	P205		-	-	-	-	23
	TS00				SCL0_B					GTIW_A		P204		-	-	-	-	24
						_			_					E3	16	19	19	25
26 20 20 17 E4 MD P201												P201	MD	E4	17	20	20	26
27 21 21 18 E5 P200	NMI											P200		E5	18	21	21	27
28 P304 GTIOC1A B												P304	1	-	-	-	-	28
29 P303 GTIOC1B	TS02	t		t					GTIOC1B			P303	1	-	-	-	-	29
30 22 22 P302 GTOUUP GTIOC4A SSLB3_B	TS08 IRQ5	t		SSLB3_B					GTIOC4A			P302	1	-	-	22	22	30
31 23 23 19 - P301 GTOULO GTIOC4B SSLB2_B	TS09 IRQ6			SSLB2_B					GTIOC4B	GTOULO		P301	1	-	19	23	23	31
32 24 24 20 F6 SWCLK P300 GTOUUP GTIOCOA SSLB1_B				SSLB1_B					GTIOC0A	GTOUUP		P300	SWCLK	F6	20	24	24	32
33 25 25 21 E6 SWDIO P108 GTOULO GTIOCOB CTS9_RT SSLB0_B _C _A S9_B/				SSLB0_B		S9_B/			GTIOC0B	GTOULO		P108	SWDIO	E6	21	25	25	33
34 26 26 22 D4 CLKOUT_ P109 GTOVUP GTIOC1A CTX0_A TXD9_B/ MOSI9_B/ SDA9_B	TS10			MOSIB_B		TXD9_B/ MOSI9_B/	CTX0_A					P109		D4	22	26	26	34

S124 Datasheet 1. Overview

		Pin numbe	•					Tin	ners		Co	ommunicati	on Interfac	es	Ana	logs	Н	МІ
LQFP64, QFN64	LQFP48	QFN48	QFN40	LGA36	Power, System, Clock, Debug, CAC	I/O ports	AGT	GPT_OPS, POEG	GРТ	RTC	USBFS,CAN	sci	)IIC	SPI	ADC14	DAC12, ACMPLP	стѕи	Interrupt
35	27	27	23	D5		P110		GTOVLO _A	GTIOC1B _A		CRX0_A	CTS0_RT S0_C/ SS0_C/ RXD9_B/ MISO9_B/ SCL9_B		MISOB_B		VCOUT	TS11	IRQ3
36	28	28	24	D6		P111			GTIOC3A _A			SCK0_C/ SCK9_B		RSPCKB_ B			TS12	IRQ4
37	29	29	25	C6		P112			GTIOC3B _A			TXD0_C/ MOSI0_C/ SDA0_C					TSCAP_C	
38	-	-	-	-		P113												
39	30	30	-	-	VCC													
40	31	31	-	-	VSS													
41	-	-	-	-		P107			GTIOC0A _B									KR07
42	-	-	-	-		P106			GTIOC0B _B					SSLA3_A				KR06
43	-	-	-	-		P105		GTETRG A_C	_5					SSLA2_A				KR05/ IRQ0
44	32	32	26	-		P104		GTETRG B_B				RXD0_C/ MISO0_C/ SCL0_C		SSLA1_A			TS13	KR04/ IRQ1
45	33	33	27	C3		P103		GTOWUP _A	GTIOC2A _A		CTX0_C	CTS0_RT S0_A/ SS0_A		SSLA0_A	AN019	CMPREF 1	TS14	KR03
46	34	34	28	C4		P102	AGTO0	GTOWLO _A	GTIOC2B _A		CRX0_C	SCK0_A		RSPCKA_ A	AN020/ ADTRG0_ A	CMPIN1	TS15	KR02
47	35	35	29	C5		P101	AGTEE0	GTETRG B_A	GTIOC5A _A			TXD0_A/ MOSI0_A/ SDA0_A/ CTS1_RT S1_A/ SS1_A	SDA1_B	MOSIA_A	AN021	CMPREF 0	TS16	KR01/ IRQ1
48	36	36	30	B6		P100	AGTIO0_ A	GTETRG A_A	GTIOC5B _A			RXD0_A/ MISO0_A/ SCL0_A/ SCK1_A	SCL1_B	MISOA_A	AN022	CMPIN0	TS26	KR00/ IRQ2
49	37	37	-	-		P500	AGTOA0	GTIU_B	GTIOC2A _B						AN016		TS27	
50	-	-	-	-		P501	AGTOB0	GTIV_B	GTIOC2B _B						AN017			
51	-	-	-	-		P502		GTIW_B	GTIOC3B _B						AN018			
52	38	38	31	A6		P015			_						AN010		TS28	IRQ7
53	39	39	32	A5		P014									AN009	DA0		
54	40	40	33	B5		P013									AN008			
55	41	41	34	B4		P012									AN007			
56	42	42	35	A4	AVCC0													
57	43	43	36	A3	AVSS0													
58	44	44	37	В3	VREFL0	P011									AN006		TS31	
59	45	45	38	A2	VREFH0	P010									AN005		TS30	
60	-	-	-	-		P004									AN004		TS25	IRQ3
61	-	-	-	-		P003									AN003		TS24	
62	46	46	-	-		P002									AN002		TS23	IRQ2
63	47	47	39	-		P001									AN001		TS22	IRQ7
64	48	48	40	B2		P000									AN000		TS21	IRQ6

Note: Several pin names have the added suffix of \_A, \_B, \_C, and \_D. The suffix can be ignored when assigning functionality.

Table 2.2 Recommended operating conditions

Parameter	Symbol	Value	Min	Тур	Max	Unit
Power supply voltages	VCC*1, *2	When USBFS is not used	1.6	-	5.5	V
		When USBFS is used USB Regulator Disable	VCC_USB	-	3.6	V
		When USBFS is used USB Regulator Enable	VCC_USB _LDO	-	5.5	V
	VSS	•	-	0	-	V
USB power supply voltages	VCC_USB	When USBFS is not used	-	VCC	-	V
		When USBFS is used USB Regulator Disable (Input)	3.0	3.3	3.6	V
	VCC_USB_LDO	When USBFS is not used	-	VCC	-	V
		When USBFS is used USB Regulator Enable	3.8	-	5.5	V
		When USBFS is used USB Regulator Disable	-	VCC	-	V
	VSS_USB	•	-	0	-	V
Analog power supply voltages	AVCC0*1, *2		1.6	-	5.5	V
	AVSS0		-	0	-	V
	VREFH0	When used as	1.6	-	AVCC0	V
	VREFL0	ADC14 Reference	-	0	-	V

Note 1. Use AVCC0 and VCC under the following conditions:

AVCC0 and VCC can be set individually within the operating range when VCC ≥ 2.2 V and AVCC0 = VCC when VCC < 2.2 V or AVCC0 < 2.2 V.

Note 2. When powering on the VCC and AVCC0 pins, power them on at the same time or the VCC pin first and then the AVCC0 pin.

# 2.2.5 I/O Pin Output Characteristics of Low Drive Capacity

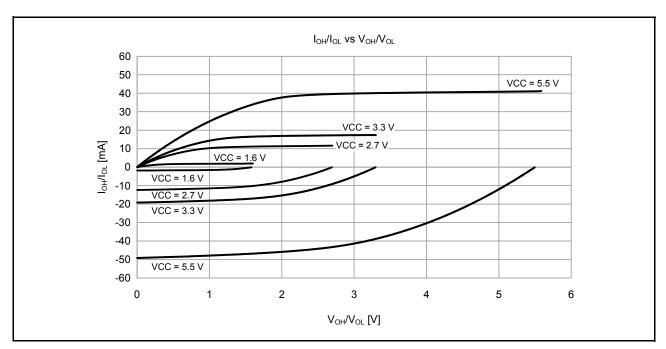


Figure 2.2  $V_{OH}/V_{OL}$  and  $I_{OH}/I_{OL}$  voltage characteristics at Ta = 25°C when low drive output is selected (reference data)

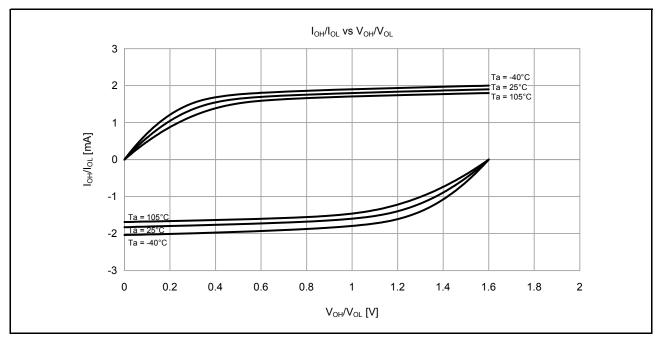


Figure 2.3  $V_{OH}/V_{OL}$  and  $I_{OH}/I_{OL}$  temperature characteristics at VCC = 1.6 V when low drive output is selected (reference data)

#### Operating and Standby Current 2.2.9

Table 2.11 Operating and standby current (1) (1 of 2) Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter	·				Symbol	Typ*9	Max	Unit	Test Conditions
Supply	High-speed	Normal mode	All peripheral clock	ICLK = 32 MHz	I <sub>CC</sub>	3.6	-	mA	*7
urrent*1	mode*2		disabled, while (1) code executing from flash*5	ICLK = 16 MHz		2.4	-		
			_	ICLK = 8 MHz		1.7	-		
			All peripheral clock	ICLK = 32 MHz		5.6	-		
			disabled, CoreMark code executing from flash*5	ICLK = 16 MHz		3.5	-		
				ICLK = 8 MHz		2.4	-		
			All peripheral clock	ICLK = 32 MHz		9.5	-		*8
			enabled, while (1) code executing from flash*5	ICLK = 16 MHz		5.4	-		
				ICLK = 8 MHz		3.3	-		
			All peripheral clock enabled, code executing from flash*5	ICLK = 32 MHz		-	21.0		
		Sleep mode	All peripheral clock	ICLK = 32 MHz		1.5	-		*7
			disabled*5	ICLK = 16 MHz		1.1	-		
				ICLK = 8 MHz		0.9	-	- - - -	
			All peripheral clock	ICLK = 32 MHz		7.2	-		*8
			enabled*5	ICLK = 16 MHz		4.0	-		
				ICLK = 8 MHz		2.4	-		
		Increase during	BGO operation*6			2.5	-		-
	Middle-speed	Normal mode	All peripheral clock	ICLK = 12 MHz	I <sub>CC</sub>	1.7	-	mA	*7
	mode*2		disabled, while (1) code executing from flash*5	ICLK = 8 MHz		1.5	-		
		All peripheral clock	ICLK = 12 MHz		2.7	-			
		disabled, CoreMark code executing from flash*5	ICLK = 8 MHz		1.9	-			
			All peripheral clock	ICLK = 12 MHz		3.9	-		*8
			enabled, while (1) code executing from flash*5	ICLK = 8 MHz		3.0	-		
			All peripheral clock enabled, code executing from flash*5	ICLK = 12 MHz		-	8.0		
		Sleep mode	All peripheral clock	ICLK = 12 MHz		0.8	-		*7
			disabled*5	ICLK = 8 MHz		0.8	-		
			All peripheral clock	ICLK = 12 MHz		2.9	-		*8
			enabled*5	ICLK = 8 MHz		2.2	-		
		Increase during	BGO operation*6			2.5	-		-
	Low-speed mode*3	Normal mode	All peripheral clock disabled, while (1) code executing from flash*5	ICLK = 1 MHz	I <sub>CC</sub>	0.2	-	mA	*7
			All peripheral clock disabled, CoreMark code executing from flash*5	ICLK = 1 MHz		0.3	-		
		All peripheral clock enabled, while (1) code executing from flash*5	ICLK = 1 MHz		0.4	-		*8	
			All peripheral clock enabled, code executing from flash*5	ICLK = 1 MHz		-	2.0		
		Sleep mode	All peripheral clock disabled*5	ICLK = 1 MHz		0.2	-		*7
		All peripheral clock enabled*5	ICLK = 1 MHz		0.3	-		*8	

## 2.2.10 VCC Rise and Fall Gradient and Ripple Frequency

Table 2.14 Rise and fall gradient characteristics

Conditions: VCC = AVCC0 = 0 to 5.5 V

Parameter		Symbol	Min	Тур	Max	Unit	Test conditions
Power-on VCC	Voltage monitor 0 reset disabled at startup	SrVCC	0.02	-	2	ms/V	-
rising gradient	Voltage monitor 0 reset enabled at startup*1, *2		0.02	-	-		
	SCI Boot mode*2		0.02	-	2		

Note 1. When OFS1.LVDAS = 0.

Note 2. At boot mode, the reset from voltage monitor 0 is disabled regardless of the value of OFS1.LVDAS bit.

## Table 2.15 Rising and falling gradient and ripple frequency characteristics

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

The ripple voltage must meet the allowable ripple frequency  $f_{r(VCC)}$  within the range between the VCC upper limit (5.5 V) and lower limit (1.6 V).

When the VCC change exceeds VCC ±10%, the allowable voltage change rising and falling gradient dt/dVCC must be met.

Parameter	Symbol	Min	Тур	Max	Unit	Test conditions
Allowable ripple frequency	f <sub>r (VCC)</sub>	-	-	10	kHz	Figure 2.24 V <sub>r (VCC)</sub> ≤ VCC × 0.2
		-	-	1	MHz	Figure 2.24 V <sub>r (VCC)</sub> ≤ VCC × 0.08
		-	-	10	MHz	Figure 2.24 V <sub>r (VCC)</sub> ≤ VCC × 0.06
Allowable voltage change rising and falling gradient	dt/dVCC	1.0	-	-	ms/V	When VCC change exceeds VCC ±10%

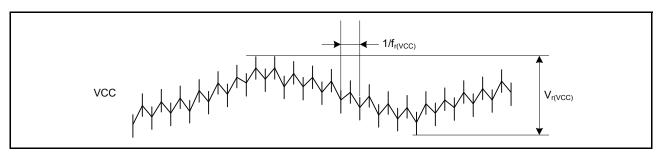


Figure 2.24 Ripple waveform

### 2.3 AC Characteristics

## 2.3.1 Frequency

Table 2.16 Operation frequency in high-speed operating mode

Conditions: VCC = AVCC0 = 2.4 to 5.5 V

Parameter			Symbol	Min	Тур	Max*5	Unit
Operation	System clock (ICLK)*1, *2, *4	2.7 to 5.5 V	f	0.032768	-	32	MHz
frequency		2.4 to 2.7 V		0.032768	-	16	
	Peripheral module clock (PCLKB)*4	2.7 to 5.5 V		-	-	32	
		2.4 to 2.7 V		-	-	16	
	Peripheral module clock (PCLKD)*3, *4	2.7 to 5.5 V		-	-	64	
		2.4 to 2.7 V		-	-	16	

- Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory. When using ICLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 2. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKD is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
- Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
- Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

Table 2.17 Operation frequency in middle-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Тур	Max*5	Unit			
Operation	System clock (ICLK)*1, *2, *4	2.7 to 5.5 V	f	0.032768	-	12	MHz			
frequency		2.4 to 2.7 V		0.032768	-	12				
		1.8 to 2.4 V		0.032768	-	8				
	Peripheral module clock (PCLKB)*4	2.7 to 5.5 V		-	-	12				
		2.4 to 2.7 V		-	-	12				
		1.8 to 2.4 V		-	-	8				
	Peripheral module clock (PCLKD)*3, *4	2.7 to 5.5 V		-	-	12				
		2.4 to 2.7 V		1	1		-	-	12	
		1.8 to 2.4 V		-	-	8				

- Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory. When using ICLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 2. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKD is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
- Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
- Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

Table 2.18 Operation frequency in low-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Тур	Max*5	Unit
Operation	System clock (ICLK)*1, *2, *4	1.8 to 5.5 V	f	0.032768	-	1	MHz
frequency	Peripheral module clock (PCLKB)*4	1.8 to 5.5 V		-	-	1	
	Peripheral module clock (PCLKD)*3, *4	1.8 to 5.5 V		-	-	1	

- Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory.
- Note 2. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKD is 1 MHz when the A/D converter is in use.
- Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
- Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

Table 2.19 Operation frequency in low-voltage mode

Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter			Symbol	Min	Тур	Max*5	Unit
Operation	System clock (ICLK)*1, *2, *4	1.6 to 5.5 V	f	0.032768	-	4	MHz
frequency	Peripheral module clock (PCLKB)*4	1.6 to 5.5 V		-	-	4	
	Peripheral module clock (PCLKD)*3, *4	1.6 to 5.5 V		-	-	4	

- Note 1. The lower-limit frequency of ICLK is 1 MHz while programming or erasing the flash memory. When using ICLK for programming or erasing the flash memory at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 2. The frequency accuracy of ICLK must be  $\pm 3.5\%$  while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.
- Note 3. The lower-limit frequency of PCLKD is 4 MHz at 2.4 V or above and 1 MHz at below 2.4 V when the 14-bit A/D converter is in use.
- Note 4. See section 8, Clock Generation Circuit in User's Manual for the relationship of frequencies between ICLK, PCLKB, and PCLKD.
- Note 5. The maximum value of operation frequency does not include internal oscillator errors. For details on the range of guaranteed operation, see Table 2.21, Clock timing.

Table 2.20 Operation frequency in Subosc-speed mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V

Parameter			Symbol	Min	Тур	Max	Unit
Operation	System clock (ICLK)*1, *3	1.8 to 5.5 V	f	27.8528	32.768	37.6832	kHz
frequency	Peripheral module clock (PCLKB)*3	1.8 to 5.5 V		-	-	37.6832	
	Peripheral module clock (PCLKD)*2, *3	1.8 to 5.5 V		-	-	37.6832	

- Note 1. Programming and erasing the flash memory is not possible.
- Note 2. The 14-bit A/D converter cannot be used.
- Note 3. See section 8, Clock Generation Circuit in User's Manual for the relationship between ICLK, PCLKB, and PCLKD frequencies.

# 2.3.6 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 Trigger Timing

Table 2.30 I/O Ports, POEG, GPT, AGT, KINT, and ADC14 trigger timing

Parameter			Symbol	Min	Max	Unit	Test conditions
I/O Ports	Input data pulse width		t <sub>PRW</sub>	1.5	-	t <sub>Pcyc</sub>	Figure 2.35
POEG	POEG input trigger pulse width		t <sub>POEW</sub>	o <sub>OEW</sub> 3		t <sub>Pcyc</sub>	Figure 2.36
GPT	Input capture pulse width	Single edge	t <sub>GTICW</sub>	1.5	-	t <sub>PDcyc</sub>	Figure 2.37
		Dual edge		2.5	-		
AGT	AGTIO, AGTEE input cycle	2.7 V ≤ VCC ≤ 5.5 V	t <sub>ACYC</sub> *1	250	-	ns	Figure 2.38
		2.4 V ≤ VCC < 2.7 V		500	-	ns	
		1.8 V ≤ VCC < 2.4 V		1000	-	ns	
	AGTIO, AGTEE input high level width, low-level width	1.6 V ≤ VCC < 1.8 V		2000	-	ns	
		2.7 V ≤ VCC ≤ 5.5 V	t <sub>ACKWH</sub> ,	100	-	ns	
		2.4 V ≤ VCC < 2.7 V	t <sub>ACKWL</sub>	200	-	ns	
		1.8 V ≤ VCC < 2.4 V		400	-	ns	
		1.6 V ≤ VCC < 1.8 V		800	-	ns	
	AGTIO, AGTO, AGTOA, AGTOB	2.7 V ≤ VCC ≤ 5.5 V	t <sub>ACYC2</sub>	62.5	-	ns	Figure 2.38
	output cycle	2.4 V ≤ VCC < 2.7 V		125	-	ns	
		1.8 V ≤ VCC < 2.4 V		250	-	ns	
		1.6 V ≤ VCC < 1.8 V		500	-	ns	
ADC14	14-bit A/D converter trigger input p	ulse width	t <sub>TRGW</sub>	1.5	-	t <sub>Pcyc</sub>	Figure 2.39
KINT	KRn (n = 00 to 07) pulse width		t <sub>KR</sub>	250	-	ns	Figure 2.40

Note: tPcyc: PCLKB cycle, tPDcyc: PCLKD cycle.

Note 1. Constraints on AGTIO input:  $t_{Pcyc} \times 2 (t_{Pcyc}: PCLKB cycle) < t_{ACYC}$ .

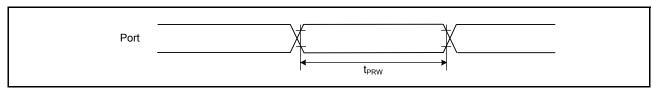


Figure 2.35 I/O ports input timing

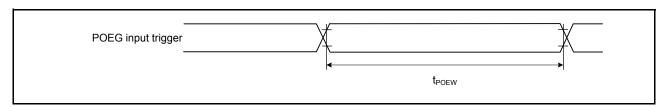


Figure 2.36 POEG input trigger timing

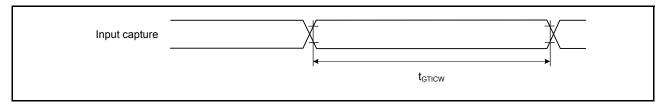


Figure 2.37 GPT input capture timing

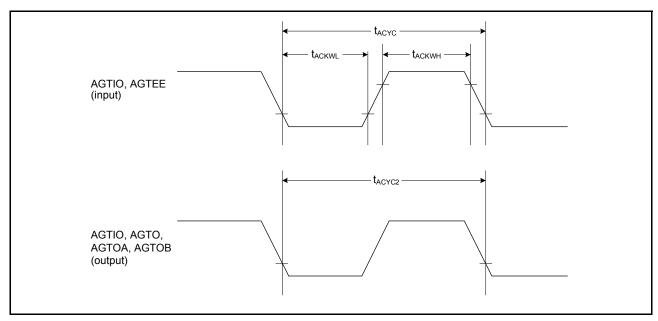


Figure 2.38 AGT I/O timing

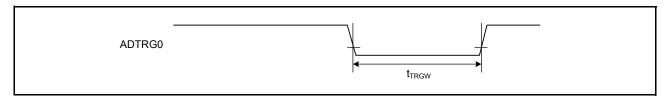


Figure 2.39 ADC14 trigger input timing

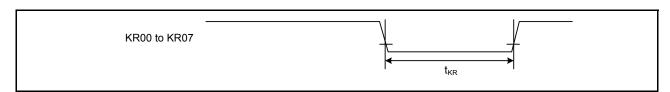


Figure 2.40 Key interrupt input timing

## 2.3.7 CAC Timing

Table 2.31 CAC timing

Paramete	er		Symbol	Min	Тур	Max	Unit	Test conditions
CAC	CACREF input pulse width	t <sub>PBcyc</sub> ≤ tcac*2	t <sub>CACREF</sub>	$4.5 \times t_{cac} + 3 \times t_{PBcyc}$	-	-	ns	-
		t <sub>PBcyc</sub> > tcac*2		$5 \times t_{cac} + 6.5 \times t_{PBcyc}$	-	-	ns	

Note 1.  $t_{PBcyc}$ : PCLKB cycle.

**Table 2.33 SCI timing (2)** Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parame	ter			Symbol	Min	Max	Unit*1	Test conditions	
Simple	SCK clock cycle outp	ut (master)	)	t <sub>SPcyc</sub>	4	65536	t <sub>Pcyc</sub>	Figure 2.43	
SPI	SCK clock cycle inpu	t (slave)			6	65536	7		
	SCK clock high pulse	width		t <sub>SPCKWH</sub>	0.4	0.6	t <sub>SPcyc</sub>	1	
	SCK clock low pulse	width		t <sub>SPCKWL</sub>	0.4	0.6	t <sub>SPcyc</sub>		
	SCK clock rise and fa	all time	1.8V or above	t <sub>SPCKr</sub> ,	-	20	ns		
			1.6V or above	t <sub>SPCKf</sub>	-	30			
	Data input setup	Master	2.7V or above	t <sub>SU</sub>	45	-	ns	Figure 2.44 to	
	time		2.4V or above		55	-		Figure 2.47	
			1.8V or above		80	-			
			1.6V or above		110	-			
		Slave	2.7V or above		40	-			
			1.6V or above		45	-			
	Data input hold time	Master		t <sub>H</sub>	33.3	-	ns		
		Slave			40	-			
	SS input setup time			t <sub>LEAD</sub>	1	-	t <sub>SPcyc</sub>		
	SS input hold time			t <sub>LAG</sub>	1	-	t <sub>SPcyc</sub>		
	Data output delay	Master	1.8V or above	t <sub>OD</sub>	-	40	ns		
			1.6V or above		-	50			
		Slave	2.4V or above		-	65			
			1.8V or above		-	100			
			1.6V or above		-	125			
	Data output hold	Master	2.7V or above	t <sub>OH</sub>	-10	-	ns		
	time		2.4V or above		-20	-			
			1.8V or above		-30	-			
			1.6V or above		-40	-			
		Slave	1		-10	-			
	Data rise and fall	Master	1.8V or above	t <sub>Dr,</sub> t <sub>Df</sub>	-	20	ns		
	time		1.6V or above		-	30			
		Slave	1.8V or above		-	20			
			1.6V or above		-	30			
Simple SPI	Slave access time			t <sub>SA</sub>	-	6	t <sub>Pcyc</sub>	Figure 2.47	
ori	Slave output release	time		t <sub>REL</sub>	-	6	t <sub>Pcyc</sub>		

Note 1.  $t_{Pcyc}$ : PCLKB cycle

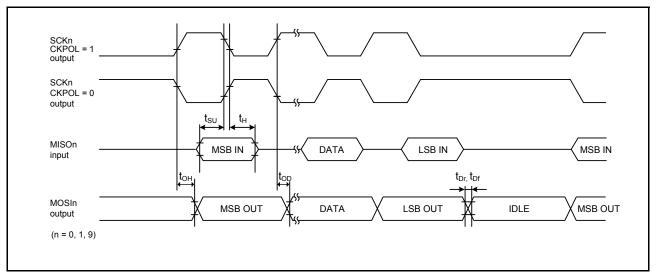


Figure 2.45 SCI simple SPI mode timing (master, CKPH = 0)

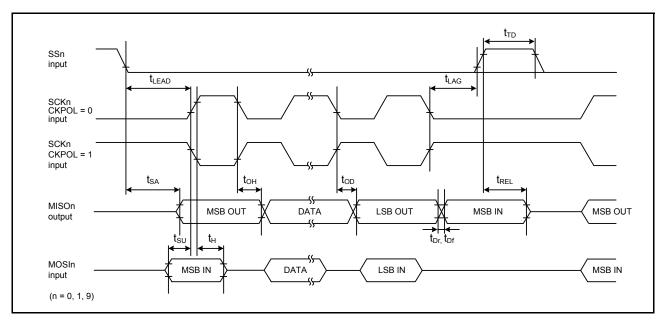


Figure 2.46 SCI simple SPI mode timing (slave, CKPH = 1)

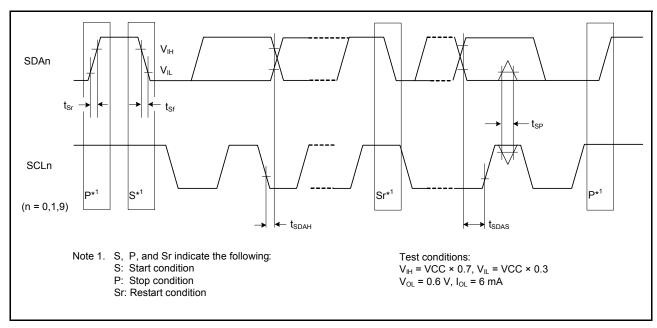


Figure 2.48 SCI simple IIC mode timing

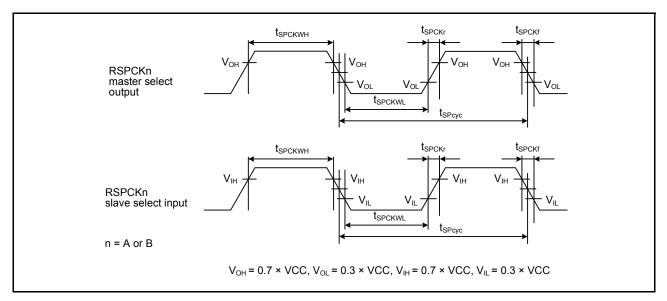


Figure 2.49 SPI clock timing

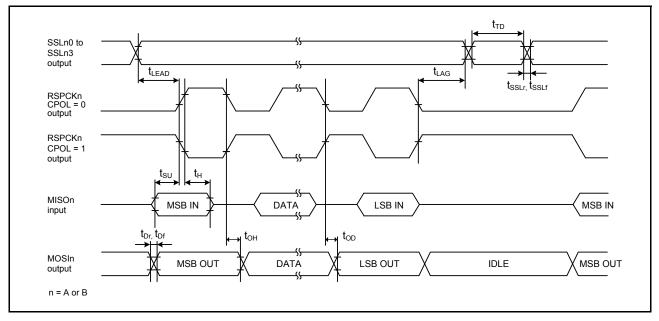


Figure 2.50 SPI timing (master, CPHA = 0) (bit rate: PCLKB division ratio is set to any value other than 1/2)

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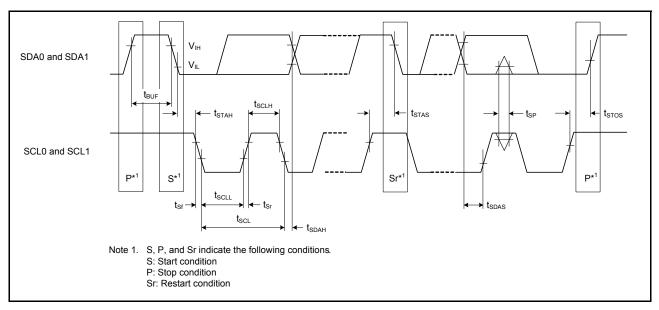


Figure 2.56 I<sup>2</sup>C bus interface input/output timing

## 2.12 Flash Memory Characteristics

## 2.12.1 Code Flash Memory Characteristics

Table 2.56 Code flash characteristics (1)

Parameter		Symbol	Min	Тур	Max	Unit	Conditions
Reprogramming/erasure cycle*1		N <sub>PEC</sub>	1000	-	-	Times	-
Data hold time	After 1000 times N <sub>PEC</sub>	t <sub>DRP</sub>	20*2, *3	-	-	Year	T <sub>a</sub> = +85°C

- Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 1,000), erasing can be performed n times for each block. For instance, when 4-byte programming is performed 256 times for different addresses in 1-KB blocks, and then the entire block is erased, the reprogram/ erase cycle is counted as 1. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited.)
- Note 2. Characteristic when using the flash memory programmer and the self-programming library provided by Renesas Electronics.
- Note 3. This result is obtained from reliability testing.

Table 2.57 Code flash characteristics (2)

High-speed operating mode

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

			ICLK = 1 MHz				ICLK = 32 MHz			
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit	
Programming time	4-byte	t <sub>P4</sub>	-	116	998	-	54	506	μs	
Erasure time	1-KB	t <sub>E1K</sub>	-	9.03	287	-	5.67	222	ms	
Blank check time	4-byte	t <sub>BC4</sub>	-	-	56.8	-	-	16.6	μs	
	1-KB	t <sub>BC1K</sub>	-	-	1899	-	-	140	μs	
Erase suspended time		t <sub>SED</sub>	-	-	22.5	-	-	10.7	μs	
Startup area switching s	etting time	t <sub>SAS</sub>	-	21.9	585	-	12.1	447	ms	
Access window time		t <sub>AWS</sub>	-	21.9	585	-	12.1	447	ms	
OCD/serial programmer	ID setting time	t <sub>OSIS</sub>	-	21.9	585	-	12.1	447	ms	
Flash memory mode transition wait time 1		t <sub>DIS</sub>	2	-	-	2	-	-	μs	
Flash memory mode tra time 2	nsition wait	t <sub>MS</sub>	5	-	-	5	-	-	μs	

- Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
- Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.



Table 2.58 Code flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

				ICLK = 1 I	ИНz		ICLK = 8 MHz		
Parameter	Parameter		Min	Тур	Max	Min	Тур	Max	Unit
Programming time	4-byte	t <sub>P4</sub>	-	157	1411	-	101	966	μs
Erasure time	1-KB	t <sub>E1K</sub>	-	9.10	289	-	6.10	228	ms
Blank check time	2-byte	t <sub>BC4</sub>	-	-	87.7	-	-	52.5	μs
	1-KB	t <sub>BC1K</sub>	-	-	1930	-	-	414	μs
Erase suspended time	Erase suspended time		-	-	32.7	-	-	21.6	μs
Startup area switching	setting time	t <sub>SAS</sub>	-	22.8	592	-	14.2	465	ms
Access window time		t <sub>AWS</sub>	-	22.8	592	-	14.2	465	ms
OCD/serial programm	er ID setting time	t <sub>OSIS</sub>	-	22.8	592	-	14.2	465	ms
Flash memory mode transition wait time 1		t <sub>DIS</sub>	2	-	-	2	-	-	μs
Flash memory mode t time 2	ransition wait	t <sub>MS</sub>	720	-	-	720	-	-	ns

- Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
- Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

## 2.12.2 Data Flash Memory Characteristics

Table 2.59 Data flash characteristics (1)

Parameter		Symbol	Min	Тур	Max	Unit	Conditions
Reprogramming/	erasure cycle*1	N <sub>DPEC</sub>	100000	1000000	-	Times	-
Data hold time	After 10000 times of N <sub>DPEC</sub>	t <sub>DDRP</sub>	20*2, *3	-	-	Year	Ta = +85°C
	After 100000 times of N <sub>DPEC</sub>		5*2, *3	-	-	Year	
	After 1000000 times of N <sub>DPEC</sub>		-	1*2, *3	-	Year	Ta = +25°C

- Note 1. The reprogram/erase cycle is the number of erasure for each block. When the reprogram/erase cycle is n times (n = 100,000), erasing can be performed n times for each block. For instance, when 1-byte programming is performed 1,000 times for different addresses in 1-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as 1. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited.)
- Note 2. Characteristics when using the flash memory programmer and the self-programming library provided by Renesas Electronics.
- Note 3. These results are obtained from reliability testing.



Table 2.60 Data flash characteristics (2)

High-speed operating mode

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

				ICLK = 4	MHz		ICLK = 32 MHz		
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Programming time	1-byte	t <sub>DP1</sub>	-	52.4	463	-	42.1	387	μs
Erasure time	1-KB	t <sub>DE1K</sub>	-	8.98	286	-	6.42	237	ms
Blank check time	1-byte	t <sub>DBC1</sub>	-	-	24.3	-	-	16.6	μs
	1-KB	t <sub>DBC1K</sub>	-	-	1872	-	-	512	μs
Suspended time during erasing		t <sub>DSED</sub>	-	-	13.0	-	-	10.7	μs
Data flash STOP recovery time		t <sub>DSTOP</sub>	5	-	-	5	-	-	μs

- Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
- Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

Table 2.61 Data flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

				ICLK = 4 I	ИНz		ICLK = 8 MHz		
Parameter		Symbol	Min	Тур	Max	Min	Тур	Max	Unit
Programming time	1-byte	t <sub>DP1</sub>	-	94.7	886	-	89.3	849	μs
Erasure time	1-KB	t <sub>DE1K</sub>	-	9.59	299	-	8.29	273	ms
Blank check time	1-byte	t <sub>DBC1</sub>	-	-	56.2	-	-	52.5	μs
	1-KB	t <sub>DBC1K</sub>	-	-	2.17	-	-	1.51	ms
Suspended time during erasing		t <sub>DSED</sub>	-	-	23.0	-	-	21.7	μs
Data flash STOP recovery time		t <sub>DSTOP</sub>	720	-	-	720	-	-	ns

- Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
- Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
- Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

# Appendix 1. Package Dimensions

Information on the latest version of the package dimensions or mountings is displayed in "Packages" on the Renesas Electronics Corporation website.

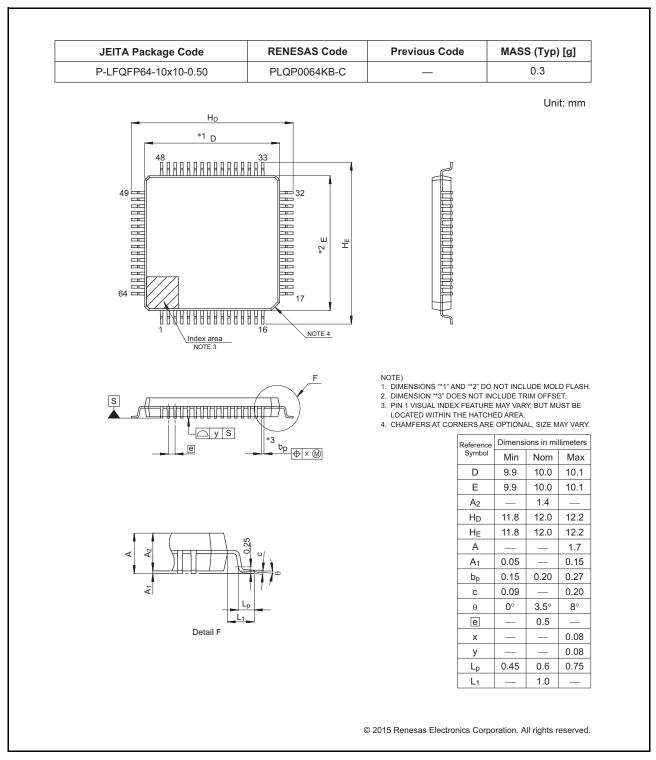


Figure 1.1 LQFP 64-pin

#### **General Precautions**

#### 1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

#### 2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

#### 3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

#### 4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

#### 5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

## 6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between  $V_{IL}$  (Max.) and  $V_{IH}$  (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between  $V_{IL}$  (Max.) and  $V_{IH}$  (Min.).

### 7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

## 8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.